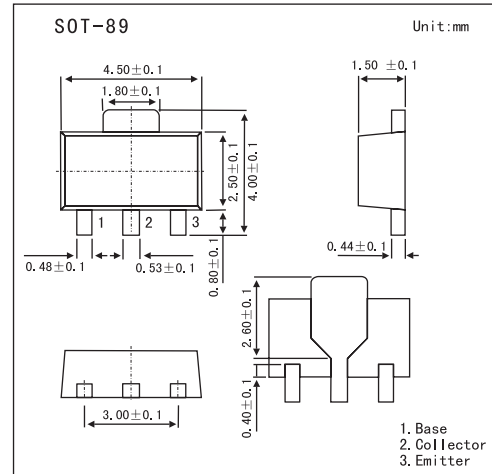


# 2SB767

## ■ Features

- Large collector power dissipation PC
- High collector-emitter voltage (Base open) V<sub>CEO</sub>
- Mini type package, allowing downsizing of the equipment and automatic



## ■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector-base voltage	V <sub>CB0</sub>	-80	V
Collector-emitter voltage	V <sub>CEO</sub>	-80	V
Emitter-base voltage	V <sub>EB0</sub>	-5	V
Collector current	I <sub>C</sub>	-1	A
Peak collector current	I <sub>CP</sub>	-0.5	A
Collector power dissipation	P <sub>C</sub>	1	W
Junction temperature	T <sub>J</sub>	150	°C
Storage temperature	T <sub>stg</sub>	-55 to +150	°C

## ■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector-base cutoff current	I <sub>CB0</sub>	V <sub>CB</sub> = -20 V, I <sub>E</sub> = 0			-0.1	μA
Collector-base voltage	V <sub>CB0</sub>	I <sub>C</sub> = -10 μA, I <sub>E</sub> = 0	-80			V
Collector-emitter voltage	V <sub>CEO</sub>	I <sub>C</sub> = -100 μA, I <sub>B</sub> = 0	-80			V
Emitter-base voltage	V <sub>EB0</sub>	I <sub>E</sub> = -10 μA, I <sub>C</sub> = 0	-5			V
Forward current transfer ratio	h <sub>FE</sub>	V <sub>CE</sub> = -10 V, I <sub>C</sub> = -150 mA	90		220	
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> = -300 mA, I <sub>B</sub> = -30 mA		-0.2	-0.4	V
Base-emitter saturation voltage	V <sub>BE(sat)</sub>	I <sub>C</sub> = -300 mA, I <sub>B</sub> = -30 mA		0.85	-1.2	V
Transition frequency	f <sub>T</sub>	V <sub>CB</sub> = -10 V, I <sub>E</sub> = 50 mA, f = 200 MHz		120		MHz
Collector output capacitance	C <sub>ob</sub>	V <sub>CB</sub> = -10 V, I <sub>E</sub> = 0, f = 1 MHz		20	30	pF

## ■ hFE Classification

Marking	CQ	CR
hFE	90~155	130~220